

Memory Module Specifications

KSM26ES8/8ME

8GB 1Rx8 1G x 72-Bit PC4-2666

CL19 288-Pin DIMM

DESCRIPTION

Kingston's KSM26ES8/8ME is a 1G x 72-bit (8GB) DDR4-2666 CL19 SDRAM (Synchronous DRAM), 1Rx8, ECC, memory module, based on nine 1G x 8-bit FBGA components. The SPD is programmed to JEDEC standard latency DDR4-2666 timing of 19-19-19 at 1.2V. Each 288-pin DIMM uses gold contact fingers. The electrical and mechanical specifications are as follows:

FEATURES

- Power Supply: VDD = 1.2V Typical
- VDDQ = 1.2V Typical
- VPP = 2.5V Typical
- VDDSPD = 2.2V to 3.6V
- Nominal and dynamic on-die termination (ODT) for data, strobe, and mask signals
- Low-power auto self refresh (LPASR)
- Data bus inversion (DBI) for data bus
- On-die VREFDQ generation and calibration
- Single-rank
- On-board I2 serial presence-detect (SPD) EEPROM
- Temperature sensor with integrated SPD
- 16 internal banks; 4 groups of 4 banks each
- Fixed burst chop (BC) of 4 and burst length (BL) of 8 via the mode register set (MRS)
- Selectable BC4 or BL8 on-the-fly (OTF)
- Fly-by topology
- Terminated control command and address bus
- PCB: Height 1.23" (31.25mm)
- RoHS Compliant and Halogen-Free

SPECIFICATIONS

CL(IDD)	19 cycles
Row Cycle Time (tRCmin)	45.75ns(min.)
Refresh to Active/Refresh Command Time (tRFCmin)	350ns(min.)
Row Active Time (tRASmin)	32ns(min.)
Maximum Operating Power	TBD W*
UL Rating	94 V - 0
Operating Temperature	0° C to +85° C
Storage Temperature	-55° C to +100° C

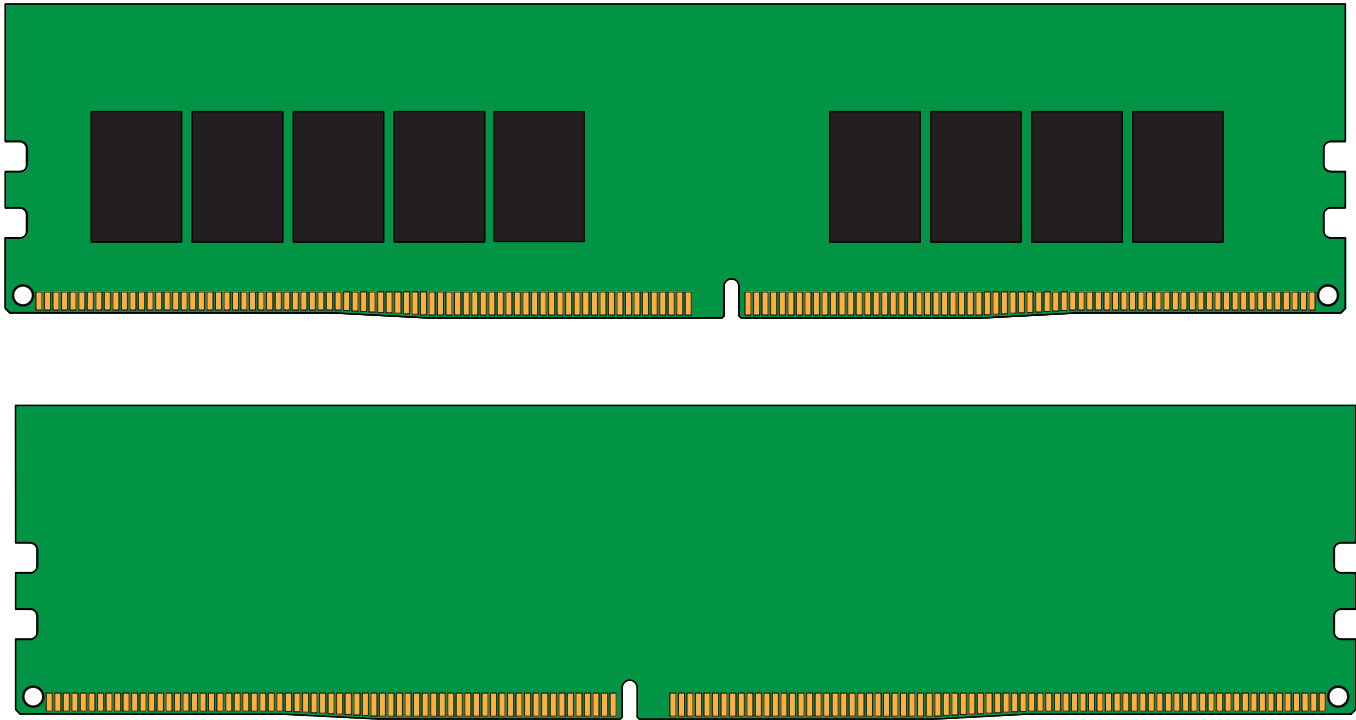
*Power will vary depending on the SDRAM used.

Module Assembly

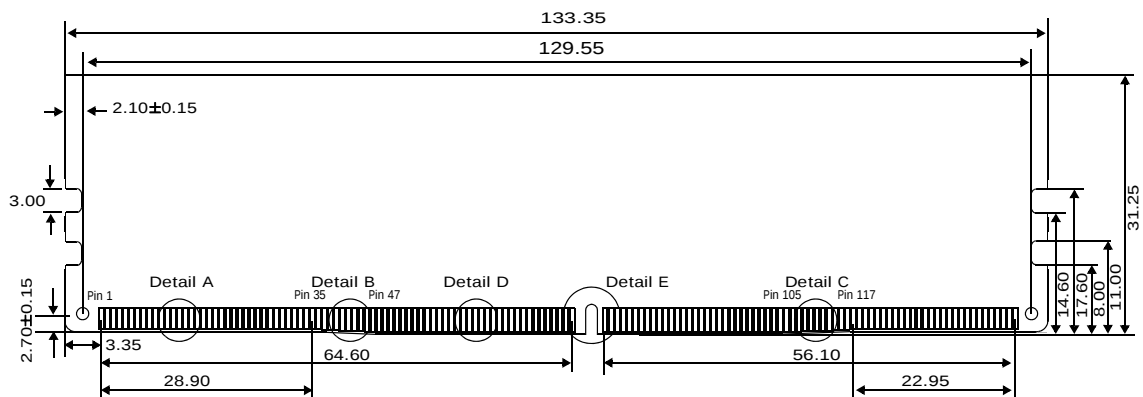
DRAM: MICRON (E-DIE)

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MODULE DIMENSIONS



All measurements are in millimeters.
(Tolerances on all dimensions are ± 0.12 unless otherwise specified)



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